











BQ2961, BQ2962

SLUSBU5G -NOVEMBER 2013-REVISED JULY 2019

BQ296xxx Overvoltage Protection for 2-Series, 3-Series, and 4-Series Cell Li-Ion Batteries with Regulated Output Supply

1 Features

- 2-series, 3-series, and 4-series cell overvoltage protection (OVP)
- Fixed delay timer to trigger FET drive output (3-s, 4-s, 5.5-s, or 6.5-s options)
- Factory programmed OVP threshold (threshold range 3.85 V to 4.6 V)
- · Output options: active high
- High-accuracy overvoltage protection: ±10 mV
- Regulated supply output with self-disable and/or external enable/disable control
 - Options: 3.3-V, 2.5-V, and 1.8-V (BQ2960, BQ2961)
 - Options: 3.3-V, 3.15-V, 3.0-V (BQ2962)
- Low power consumption I_{CC} ~ 4 μA (V_{CELL(ALL)} < V_{PROTECT})
- Extra low power consumption with reg output disabled, I_{CC} ~ 1.2 μA
- Low leakage current per cell input < 100 nA
- · Small package footprint
 - 8-Pin WSON (2 mm x 2 mm)

2 Applications

- Notebook PC
- Ultrabooks
- Medical
- UPS battery backup

3 Description

The BQ296xxx family is a high-accuracy, low-power overvoltage protector with a 2-mA regulated output supply for Li-lon battery pack applications.

Each cell in a 2-series to 4-series cell stack is individually monitored for an overvoltage condition. An internally fixed-delay timer is initiated upon detection of an overvoltage condition on any cell. Upon expiration of the delay timer, an output pin is triggered into an active state to indicate that an overvoltage condition has occurred.

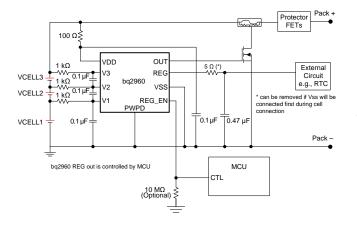
The regulated output supply delivers up to 2-mA (max) output current to drive always-on circuits, such as a real-time clock (RTC) oscillator. The BQ296xxx family has a self-disable function to turn off the regulated output if any cell voltage falls below a certain threshold, thereby preventing drain on the battery, and provides an external control to enable or disable the regulated output.

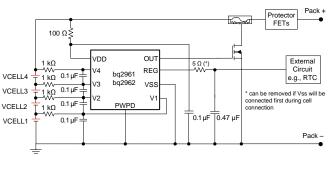
Device Information⁽¹⁾⁽²⁾

PART NUMBER	PACKAGE	BODY SIZE (NOM)
BQ2960		
BQ2961	WSON (8)	2.00 mm × 2.00 mm
BQ2962		

- (1) For all available packages, see the orderable addendum at the end of the data sheet.
- (2) The BQ2960 is a 2-series to 3-series device. The BQ2961 and BQ2962 are 2-series to 4-series devices.

Simplified Schematic





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4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision F (May 2019) to Revision G	Page
Added the BQ296223 and BQ296224 devices to the Device Comparison Table. Changes from Revision E (June 2018) to Revision F Added the BQ296215 device to the Device Comparison Table Changes from Revision D (January 2017) to Revision E Changed Description Added the BQ296221 device to the Device Comparison Table Changed Regulated Supply Output, REG Changed Detailed Design Procedure Changed Detailed Design Procedure Changed device label from "BQ2960xy" to "BQ2960" and changed device label from "BQ2961xy" to "BQ2961/BQ2962" in the Simplified Schematic Removed BQ296100 preview status. Added BQ296216, BQ296217 device spins to the Device Comparison Tale Extended IDD test condition from (Vn-Vn-1) = 3.8V to (Vn-Vn-1) = 2 V to 4.15 V	4
Changes from Revision E (June 2018) to Revision F	Page
Added the BQ296215 device to the Device Comparison Table	4
Changes from Revision D (January 2017) to Revision E	Page
Changed Description	1
Added the BQ296221 device to the <i>Device Comparison Table</i>	4
Changed Regulated Supply Output, REG	12
Changed Detailed Design Procedure	19
Changes from Revision C (October 2016) to Revision D	Page
• Removed BQ296100 preview status. Added BQ296216, BQ296217 device spins to the D	evice Comparison Table 4
• Extended I_{DD} test condition from $(V_n - V_{n-1}) = 3.8 \text{V}$ to $(V_n - V_{n-1}) = 2 \text{ V}$ to 4.15 V	7
Added V _{OUT} TYP and MAX specification	7
• Added VREG specification at 500 μA load. Was only specified with 0~1-mA range before	8
Extended IREG MAX specification to 2 mA, was 1 mA before	8
Changed device label from "BQ2960xv" "BQ2960" in Figure 13.	

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_	Added Receiving Notification of Documentation Updates section	20
CI	nanges from Revision B (May 2016) to Revision C	Page
•	Added BQ2962 REG options	1
•	Changed Part number to BQ2960, BQ2961, BQ2962 to identify each spin family throughout the data sheet	<i>*</i>
•	Added BQ296202, BQ296203, BQ296212, BQ296213	4
•	Added BQ2962 pinout	5
•	Added bq2962 device to Recommended Operating Conditions	6
•	Extended bq2962 V _{REG} full range condition from 0 mA to 2 mA, was 0 mA to 1 mA before	8
•	Added BQ2962 regulator programmable option	10
•	Changed figure title to apply to BQ2962 family	19
<u>•</u>	Changed figure title to apply to BQ2962	22
CI	nanges from Revision A (January 2016) to Revision B	Page
•	Added BQ296114 to the Device Comparison Table	
CI	nanges from Original (November 2013) to Revision A	Page
•	Changed the device listing in the data sheet header information to: BQ2961	
•	Changed BQ296106, '107, '111 From: Preview To: Released status	4
•	Added BQ296112 to the Device Comparison Table	
•	Added BQ296113 to the Device Comparison Table	
•	Added the BQ2961xy configuration range to the Device Comparison Table	4



5 Device Comparison Table

Table 1. BQ2961 Device Options

BQ2961	OVP (V)	OVP DELAY (s)	UV (V)	LDO (V)
BQ296100	4.35	6.5	2.5	3.3
BQ296103	4.50	6.5	2.5	3.3
BQ296106	4.45	6.5	2.8	3.3
BQ296107	4.50	6.5	2.8	3.3
BQ296111	4.45	4.0	2.5	3.3
BQ296112	4.50	3.0	2.5	3.3
BQ296113	4.35	3.0	2.5	3.3
BQ296114	4.50	4.0	2.5	3.3
BQ2961	3.85 V-4.60 V (50-mV step)	3.0, 4.0, 5.5, 6.5	2.0 V-2.8 V (50-mV step)	1.8, 2.5, 3.3

Table 2. BQ2962 Device Options

BQ2962	OVP (V)	OVP DELAY (s)	UV (V)	LDO (V)
BQ296202	4.45	6.5	2.5	3.3
BQ296203	4.50	6.5	2.5	3.3
BQ296212	4.50	3.0	2.5	3.3
BQ296213	4.35	3.0	2.5	3.3
BQ296215 ⁽¹⁾	4.50	6.5	2.5	3.0
BQ296216	4.55	6.5	2.5	3.0
BQ296217	4.55	6.5	2.8	3.3
BQ296221 ⁽¹⁾	4.55	6.5	2.5	3.3
BQ296223	4.50	6.5	2.5	3.3
BQ296224	4.50	6.5	2.5	3.0
BQ2962	3.85 V-4.60 V (50-mV step)	3.0, 4.0, 5.5, 6.5	2.0 V-2.8 V (50-mV step)	3, 3.15, 3.3

⁽¹⁾ Contact TI for more information.

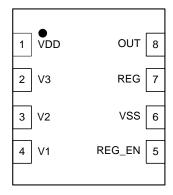
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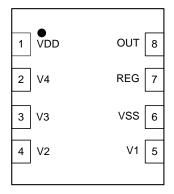


6 Pin Configuration and Functions

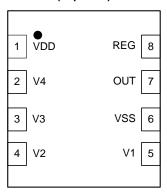
2-Series to 3-Series BQ2960 (Top View)



2-Series to 4-Series BQ2961 (Top View)



2-Series to 4-Series BQ2962 (Top View)



Pin Functions

	PIN			TYPE ⁽¹⁾	DECORIDATION	
NAME	BQ2960	BQ2961	BQ2962	TIPE	DESCRIPTION	
OUT	8	8	7	OA	Analog output drive for an overvoltage fault signal; CMOS output high or open-drain active low	
PWPD	9	9	9	Р	TI recommends connecting the exposed pad to VSS on PCB.	
REG	7	7	8	OA	Regulated supply output. Requires an external ceramic capacitor for stability	
REG_EN	5	_	_	IA	Regulated supply output enable. A "high" to enable REG output and "low" to disable REG output	
V1	4	5	5	IA	Sense input for positive voltage of the lowest cell from the bottom of the stack	
V2	3	4	4	IA	Sense input for positive voltage of the second cell from the bottom of the stack	
V3	2	3	3	IA	Sense input for positive voltage of the third cell from the bottom of the stack	
V4	_	2	2	IA	Sense input for positive voltage of the fourth cell from the bottom of the stack	
VDD	1	1	1	Р	Power supply input	
VSS	6	6	6	Р	Electrically connected to integrated circuit ground and negative terminal of the lowest cell in the stack	

(1) IA = Analog input, OA = Analog Output, P = Power connection



7 Specifications

7.1 Absolute Maximum Ratings

Over operating free-air temperature range (unless otherwise noted)⁽¹⁾

		MIN	MAX	UNIT	
Supply voltage	VDD - VSS	-0.3	30		
	V4 - V3, V3 - V2, V2 - V1, V1 - VSS	-0.3	30		
Input voltage	REG – VSS	-0.3	3.6	V	
	REG_EN - VSS	-0.3	28		
Output voltage	OUT - VSS	-0.3 30			
Continuous total power dissipation, P _{TOT}		See Thermal Information.			
Lead temperature (soldering, 10 s), T _{SOLDER}		300	300	°C	
Storage temperature, T _{stg}		-65	150	°C	

⁽¹⁾ Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Procedures. Exposure to absolute-maximum—rated conditions for extended periods may affect device reliability.

7.2 ESD Ratings

			VALUE	UNIT
\/	Floatroototic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 (1)	2000	V
V _(ESD)	Electrostatic discharge	Charged device model (CDM), per JEDEC specification JESD22-C101 (2)	500	V

⁽¹⁾ JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

7.3 Recommended Operating Conditions

Over operating free-air temperature range (unless otherwise noted).

		MIN	NOM MAX	UNIT
	Supply voltage, V _{DD} ⁽¹⁾ , bq2960	3	15	
Supply voltage, V _{DD} ⁽¹⁾	Supply voltage, V _{DD} ⁽¹⁾ , bq2961, bq2962 Supply voltage, V _{DD} with REG output on age V _n - V _{n-1} , V1 – VSS REG_EN	3	20	V
Supply voltage, V _{DD} with REG output on	4			
Input voltage	$V_n - V_{n-1}$, $V1 - VSS$	0	5	V
range	$ \begin{array}{c} \text{V voltage,} \\ \text{Supply voltage, V}_{\text{DD}}^{(1)}, \text{ bq2961, bq2962} \\ \text{Supply voltage, V}_{\text{DD}} \text{ with REG output on} \end{array} \qquad $	V		
Operating ambier	nt temperature range, T _A	-40	110	°C

⁽¹⁾ See Typical Application.

7.4 Thermal Information

		bq296xxx	
	Junction-to-case(top) thermal resistance	DSG (WSON)	UNIT
		8 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	62	°C/W
$R_{\theta JC(top)}$	Junction-to-case(top) thermal resistance	72	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	32.5	°C/W
ΨЈТ	Junction-to-top characterization parameter	1.6	°C/W
ΨЈВ	Junction-to-board characterization parameter	33	°C/W
$R_{\theta JC(bot)}$	Junction-to-case(bottom) thermal resistance	10	°C/W

For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

⁽²⁾ JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.



7.5 Electrical Characteristics

Typical values stated where T_A = 25°C and VDD = 14.4 V, MIN/MAX values stated where T_A = -40°C to +110°C, and V_{DD} = 3 V to 15 V (unless otherwise noted).

P	ARAMETER	TEST CONDITIONS	S	MIN	TYP	MAX	UNIT
Voltage Pr	otection Thresholds						
V _{OV}	V _(PROTECT) Overvoltage Detection	$R_{IN} = 1 \text{ k}\Omega$	$R_{IN} = 1 k\Omega$		Applicable Voltage: 3.85 V to 4.6 V in 50-mV steps		V
V_{HYS}	OV Detection Hysteresis			250	300	400	mV
V _{OA}	OV Detection Accuracy	T _A = 25°C		-10		10	mV
		$T_A = -40$ °C		-40		40	mV
	OV Detection	$T_A = 0$ °C		-20		20	mV
$V_{OADRIFT}$	Accuracy Across	T _A = 60°C		-24		24	mV
	Temperature	T _A = 110°C		-54		54	mV
		T _A = 110°C		-54		54	mV
Supply and	d Leakage Current					l	
_	Supply Current with	$(V_n - V_{n-1}) = 2 \text{ V to } 4.15 \text{ V, } n = 1 \text{ to } 4,$	$T_A = 0$ °C to 60 °C		4	6	μΑ
I _{DD}	REG on	$VDD = top V_n voltage$ $(V1 - V_{SS}) > V_{UVREG}$, $I_{REG} = 0 mA$,	$T_A = -40^{\circ}C \text{ to } 110^{\circ}C$			8	μΑ
	Supply Current with	$(V_n - V_{n-1}) = 2 \text{ V to } 4.15 \text{ V, } n = 1 \text{ to } 4,$	$T_A = 0$ °C to 60 °C		1	2	μΑ
I _{DD}	REG off	$VDD = top V_n voltage$ $(V1 - V_{SS}) < V_{UVREG}$	$T_A = -40^{\circ}C \text{ to } 110^{\circ}C$			4	μΑ
I _{IN}	Input Current at V _x Pins	$(V_n - V_{n-1}) = (V1 - V_{SS}) = 3.8 \text{ V}, \text{ VDD} = \text{to}$ 25°C	op V_n voltage, $T_A =$	-0.1		0.1	μΑ
Output Dri	ve OUT, CMOS Active	High					
		$(V_n - V_{n-1})$ or $(V1 - V_{SS}) > V_{OV}$, $I_{OH} = 100$ voltage	μ A, VDD = top V _n	6	7	8	V
V _{OUT}	Output Drive Voltage, Active High	If three of four cells are short circuited, on powered and $> V_{OV}$, VDD = V_n (the remail = 100 μ A			VDD - 0.3		V
		$(V_n - V_{n-1})$ and $(V1 - V_{SS}) < V_{OV}$, VDD = solution voltage, I_{OL} = 100 μ A measured into OUT			250	400	mV
I _{OUTH}	OUT Source Current (during OV)	$(V_n - V_{n-1})$, $(V3 - V2)$, or $(V1 - V_{SS}) > V_{OV}$ voltage, forced OUT = 0 V, measured out of OUT				4.5	mA
I _{OUTL}	OUT Sink Current (no OV)	$(V_n - V_{n-1})$ and $(V1 - V_{SS}) < V_{OV}$, $VDD = 1$ OUT = VDD, measured into OUT pin. Pull $k\Omega$ to VDD	$(V_n - V_{n-1})$ and $(V1 - V_{SS}) < V_{OV}$, VDD = top V_n voltage, forced OUT = VDD, measured into OUT pin. Pull-up resistor $R_{PU} = 5$			14	mA
Internal Fix	ced Delay Timer						
		Internal Fixed Delay, 3-s delay option		2.4	3	3.6	s
	OV Dolov Time (1)	Internal Fixed Delay, 4-s delay option		3.2	4	4.8	S
t _{DELAY}	OV Delay Time ⁽¹⁾	Internal Fixed Delay, 5.5-s delay option		4.4	5.5	6.6	S
		Internal Fixed Delay, 6.5-s delay option		5.2	6.5	7.8	s
t _{DELAY_CTM}	Fault Detection Delay Time in Test Mode OV Delay Time	Internal Fixed delay			15		ms

⁽¹⁾ Specified by design. Not 100% tested in production.



Electrical Characteristics (continued)

Typical values stated where $T_A = 25^{\circ}C$ and VDD = 14.4 V, MIN/MAX values stated where $T_A = -40^{\circ}C$ to +110°C, and $V_{DD} = 3$ V to 15 V (unless otherwise noted).

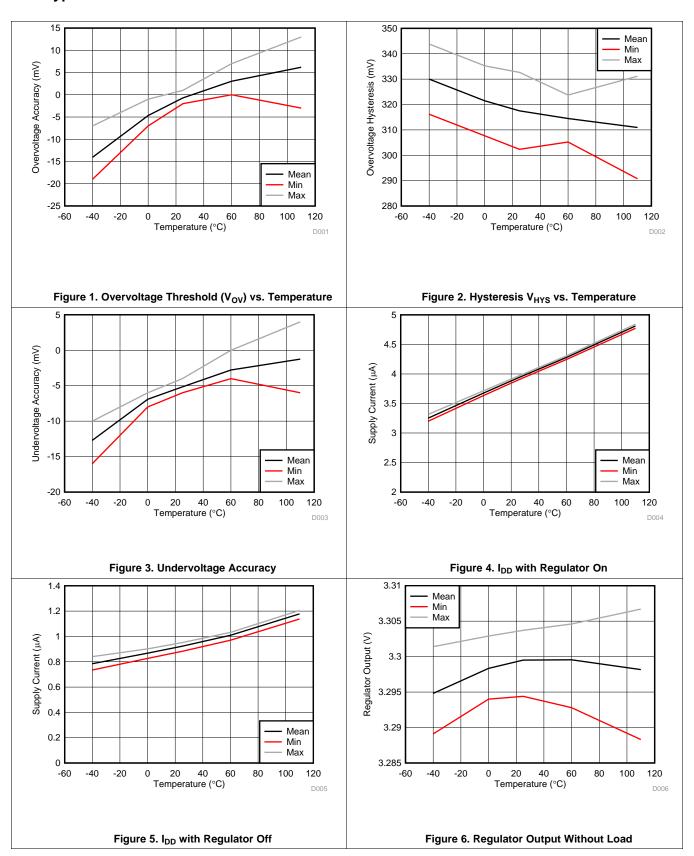
P	ARAMETER	TEST CONDITI	ONS	MIN	TYP	MAX	UNIT	
Regulated	Supply Output, REG							
			V _{REG} = 3.3 V, bq2960, bq2961, bq2962	3.234	3.300	3.366		
	REG Supply at 500 μA load		V _{REG} = 3.15 V, bq2962	3.087	3.150	3.213		
V_{REG}		$VDD \ge 4 \text{ V, I}_{REG} = 500 \mu\text{A},$ $C_{REG} = 0.47 \mu\text{F}$	V _{REG} = 3.0 V, bq2962	2.940	3.000	3.060	V	
			V _{REG} = 2.5 V, bq2960, bq2961	2.450	2.500	2.550		
			V _{REG} = 1.8 V, bq2960, bq2961	1.764	1.800	1.836		
V_REG			V _{REG} = 3.3 V, bq2960, bq2961, bq2962	3.200	3.300	3.400		
	REG Supply from 0 to 2 mA load	VDD \geq 4 V, I $_{REG}$ = 0 μ A to 2 mA, C_{REG} = 0.47 μ F	V _{REG} = 3.15 V, bq2962	3.050	3.150	3.250	V	
			V _{REG} = 3.0 V, bq2962	2.900	3.000	3.100		
			V _{REG} = 2.5 V, bq2960, bq2961	2.425	2.500	2.575		
			V _{REG} = 1.8 V, bq2960, bq2961	1.746	1.800	1.854		
I _{REG}	REG Current Output	VDD ≥ 4 V, $C_{REG} = 0.47 \mu F$		0		2	mA	
I _{REG_} SC_Limit	REG Output Short Circuit Current Limit	REG = V_{SS} , $C_{REG} = 0.47 \mu F$		4			mA	
R _{REG_PD}	REG pull-down resistor	REG is disabled.		20	30	45	kΩ	
Regulated	Supply Output Enable	e, REG_EN						
V_{IH}	High-level Input			1.6			V	
V_{IL}	Low-level Input					0.4	V	
I _{LKG}	Input Leakage Current	V _{IH} < 6 V				0.1	μΑ	
Regulated	Supply Undervoltage	Self-Disable						
V_{UVREG}	Undervoltage detection	Factory Configuration: 2.0 V to 2.8 V i	in 50 mV steps, T _A = 25°C	-50		50	mV	
V _{UVHYS}	Undervoltage Detection Hysteresis			250	300	400	mV	
t _{UVDELAY}	Undervoltage Detection Delay			4.5	6	7.5	S	
V _{UVQUAL}	Cell voltage to qualify for UV detection				0.5		V	

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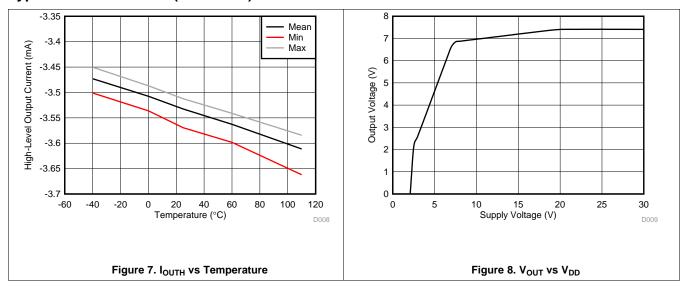


7.6 Typical Characteristics



TEXAS INSTRUMENTS

Typical Characteristics (continued)



8 Detailed Description

8.1 Overview

The BQ2960, BQ2961, and BQ2962 are second-level overvoltage (OV) protectors with a regulated output. Each cell is monitored independently by comparing the actual cell voltage to an overvoltage threshold V_{OV} . The overvoltage threshold is preprogrammed at the factory with a range between 3.85 V to 4.65 V.

The regulated output is enabled unless any of the cell voltages fall below the V_{UVREG} threshold. This threshold is preprogrammed at the factory with a range between 2 V to 2.8 V. For BQ2960xy family, an external control pin, REG_EN, is available to enable or disable the regulated output in addition to the V_{UVREG} detection.

Table 3. Programmable Parameters

OVERVOLTAGE RANGE (V)	OVERVOLTAGE DELAY (s)	UNDERVOLTAGE RANGE (V)	REGULATOR (V)
3.85 to 4.6 in 50-mV step	3, 4, 5.5, 6.5		1.8, 2.5, 3.3 (BQ2960, BQ2961) 3.0, 3.15, 3.3 (BQ2962)



8.2 Functional Block Diagram

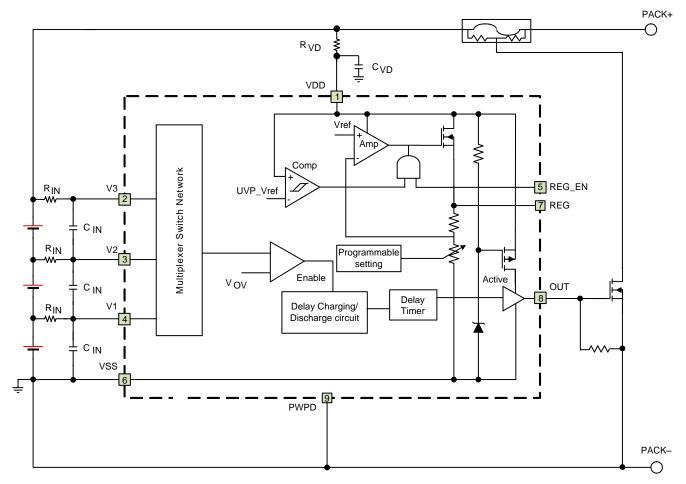


Figure 9. BQ2960 Block Diagram



Functional Block Diagram (continued)

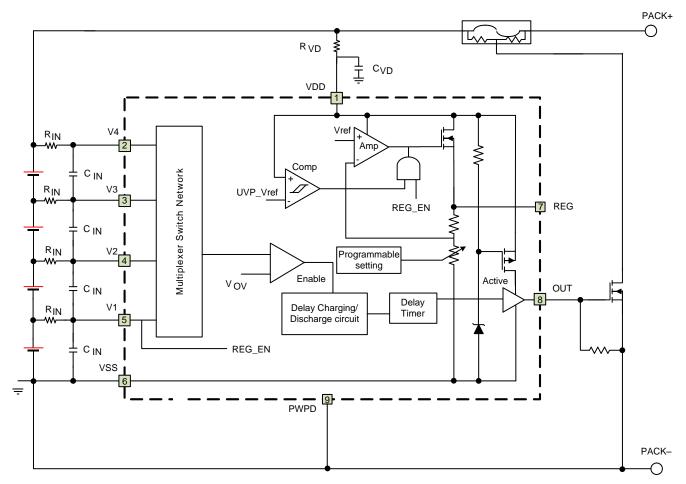


Figure 10. BQ2961 and BQ2962 Block Diagram

8.3 Feature Description

8.3.1 Pin Details

8.3.1.1 Input Sense Voltage, Vx

These inputs sense each battery cell voltage. A series resistor and a capacitor across the cell for each input is required for noise filtering and stable voltage monitoring.

8.3.1.2 Output Drive, OUT

This terminal serves as the fault signal output in active high.

8.3.1.3 Supply Input, VDD

This terminal is the unregulated input power source for the device. A series resistor is connected to limit the current, and a capacitor is connected to ground for noise filtering.

8.3.1.4 Regulated Supply Output, REG

This terminal is connected to an external capacitor and provides a regulated supply to power a circuit such as a real-time clock integrated circuit, or functions requiring a well-regulated supply. Maximum current load on this pin cannot exceed I_{REG} mA.

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Feature Description (continued)

The REG output has protection for overcurrent, using a current limit protection circuit, and also detects and protects for excessive power dissipation due to short circuit of the external load. This pin requires a ceramic 1-µF capacitor connection to VSS for improved stability, noise immunity, and ESD performance of the supply output. This capacitor must be placed close to the REG and VSS pins for connection.

8.3.1.5 Regulated Supply Output Enable, REG EN (BQ2960 Only)

This terminal is a high-voltage input drain to enable and disable the regulated supply output, REG terminal. When the VREG_EN > VIH, the REG terminal output is enabled including the cell undervoltage detection function to self-disable the regulated supply. When the VREG_EN < V_{IL}, the REG terminal output, the cell undervoltage detection and the regulated supply self-disable functions are disabled.

To keep the REG output enabled at all times, the recommendation is to connect the REG_EN to the V1 termination. There is a 6-V clamp to protect the REG_EN terminal from a high voltage input. By connecting REG_EN to V1, the clamp circuit is not active.

When the REG output is enabled, VREG_EN > VIH, the REG output can be self-disabled if any of the cell voltages are < V_{UVREG}. The self-disable function is used to reduce power consumption when the battery pack is deeply depleted.

8.3.2 Overvoltage Sensing for OUT

In the BQ296xxx device, each cell is monitored independently. Overvoltage is detected by comparing the actual cell voltage to a protection voltage reference, Vov. If any cell voltage exceeds the programmed OV value, an internal timer circuit is activated. This timer circuit causes a factory pre-programmed fixed delay before the OUT terminal goes from inactive to active state.

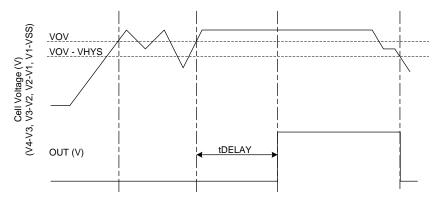


Figure 11. Timing for Overvoltage Sensing for OUT

8.3.3 Regulated Output Voltage and REG_EN Pin

For BQ2960 and BQ2961, there are three factory-preprogrammed options for the regulated output voltage, 3.3 V, 2.5 V, and 1.8 V. For BQ2962, the regulated output voltage options are 3.3 V, 3.15 V, and 3.0 V. Potentially, the BQ2962xy device can provide other regulated voltage output between 3.3 V to 3.0 V. Contact Texas Instruments for details.

At power up, the regulated output is on by default. If any cell voltage is below V_{UVREG} at device power up, the regulated output will remain on until the t_{UV DELAY} time has passed, the regulated output turns off after the delay time.

During discharge, if any cell voltage falls below the V_{UVREG} threshold for t_{UV DELAY} time, the regulated output is self-disabled. The regulated output turns on again when all the cell voltages are above V_{UVREG} + V_{UVHYS}.

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Feature Description (continued)

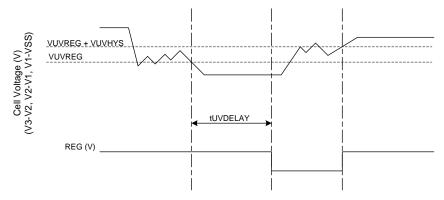
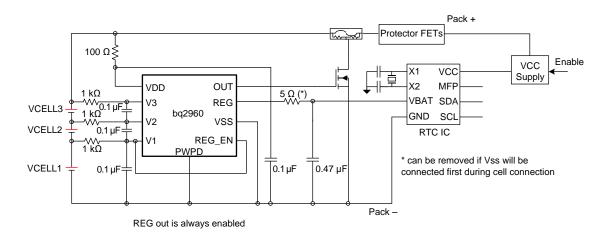


Figure 12. REG Output Timing

For the BQ2960 family, an external REG_EN pin is available to enable and disable the regulated output function. To enable both the regulated output and the undervoltage self-disable features, the REG_EN pin must be above V_{IH} . A microcontroller can be used to control the REG_EN pin. Alternatively, connecting the REG_EN pin to the bottom cell is another option to enable the regulated output function always.



Feature Description (continued)



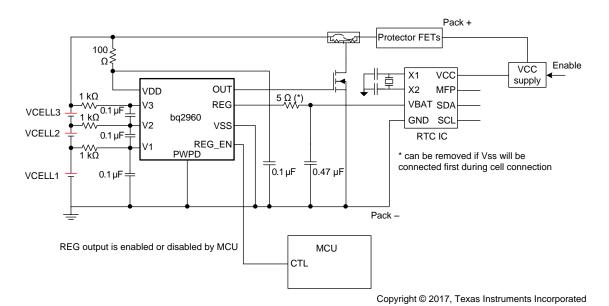


Figure 13. BQ2960 Application Schematic

8.4 Device Functional Modes

8.4.1 NORMAL Mode

When all of the cell voltages are below the V_{OV} threshold AND above V_{UVREG} threshold, the device operates in NORMAL mode. The device monitors the differential cell voltages connected across (V1–VSS), (V2–V1), (V3–V2), and (V4–V3). The OUT pin is inactive in this mode. The regulated output is always enabled for BQ2961. For BQ2960, the regulated output is on only if the voltage on the REG_EN pin is above V_{IH} .

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Device Functional Modes (continued)

8.4.2 OVERVOLTAGE Mode

OVERVOLTAGE mode is detected if any of the cell voltages exceed the overvoltage threshold, V_{OV} , for a configured OV delay time. The OUT pin is activated after a delay time preprogrammed at the factory. The OUT pin will pull high internally. Then an external FET is turned on, shorting the fuse to ground, which allows the battery and/or charger power to blow the fuse. When all of the cell voltages fall below ($V_{OV} - V_{HYS}$), the device returns to NORMAL mode. The regulated output (if enabled) remains on in this mode.

8.4.3 UNDERVOLTAGE Mode

The UNDERVOLTAGE mode is detected if any of the cell voltage across (V1–VSS), (V2–V1), (V3–V2), or (V4–V3) is below the V_{UVREG} threshold for t_{UV_DELAY} time. In this mode, the regulated output is disabled. To return to the NORMAL mode, all the cell voltages must be above ($V_{UVREG} + V_{UVHYS}$).

For a low cell configuration, V_n pin can be shorted to the (V_{n-1}) pin. The device ignores any differential cell voltage below V_{UVQUAL} threshold for undervoltage detection.

8.4.4 CUSTOMER TEST MODE

The Customer Test Mode (CTM) helps to reduce test time for checking the overvoltage delay-timer parameter once the circuit is implemented into the battery pack. To enter CTM, the VDD pin should be set at least 10 V higher than V3 (see Figure 14). The delay timer is greater than 10 ms, but considerably shorter than the timer delay in normal operation. To exit CTM, remove the VDD to VC3 voltage differential of 10 V, so that the decrease in the value automatically causes an exit.

CAUTION

Avoid exceeding any Absolute Maximum Voltages on any pins when placing the device into CTM. Also avoid exceeding Absolute Maximum Voltages for the individual cell voltages (V3–V2), (V2–V1) and (V1–VSS). Stressing the pins beyond the rated limits can cause permanent damage to the device.

Figure 14 shows the timing for the Customer Test Mode.

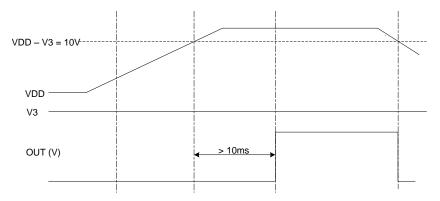


Figure 14. Timing for Customer Test Mode



Device Functional Modes (continued)

Figure 15 shows the measurement for current consumption of the product for both VDD and Vx.

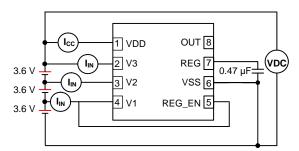


Figure 15. Configuration for Integrated Circuit Current Consumption Test



9 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

The BQ296xxx family of second-level protectors is used for overvoltage protection of the battery pack in the application. A regulated output is available to drive a small circuit with maximum I_{REG} loading. The device OUT pin is active high, which drives a NMOS FET that connects the fuse to ground in the event of a fault condition. This provides a shorted path to use the battery and/or charger power to blow the fuse and cut the power path.

9.2 Typical Application

Figure 13 shows the recommended reference design components.

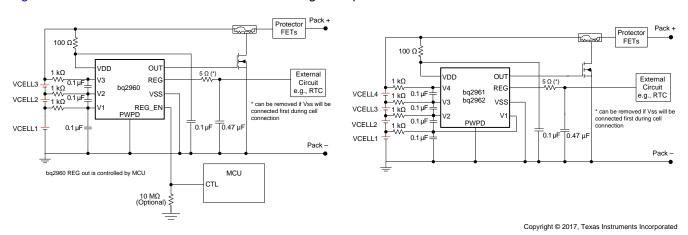


Figure 16. Application Schematic

9.2.1 Design Requirements

NOTE

Changes to the ranges shown in Table 4 will impact the accuracy of the cell measurements.

Table 4. Parameters

PARAMETER	EXTERNAL COMPONENT	MIN	NOM	MAX	UNIT
Voltage monitor filter resistance	R _{IN}	900	1000	4700	Ω
Voltage monitor filter capacitance	C _{IN}	0.01	0.1	1.0	μF
Supply voltage filter resistance	R _{VD}	0.1	_	1	ΚΩ
Supply voltage filter capacitance	C _{VD}	_	0.1	1.0	μF
REG output capacitance	C _{REG}	0.47	1	_	μF

NOTE

The device is calibrated using an R_{IN} value = 1 k Ω . Using a value other than the recommended value changes the accuracy of the cell voltage measurements and V_{OV} trigger level.



9.2.2 Detailed Design Procedure

NOTE

The device VSS must be connected first during PCB test or cell attachment. Failure to do so can damage the REG pin.

- 1. If the VSS pin cannot be connected first, it is required to add a resistor of a minimum of 5 Ω to a maximum of 10 Ω (a 5- Ω resistor is used in the reference schematic, Figure 17) in series with the REG capacitor. When VSS is floating, the REG capacitor always charges up to the VDD voltage. When VSS is finally connected, the REG capacitor will be discharged. Adding a small resistor in series reduces the current strength and avoids any potential damage to the REG pin. The 5- Ω resistor can be placed in series with the REG connect circuit (as shown in Figure 17) or in series of the REG capacitor (as shown in Figure 18). Placing the resistor in series with the REG circuit results in a small drop of V_{REG} (for example: max loading of I_{REG} mA with a 5- Ω resistor will drop 5 mV on V_{REG}), but such a connection can protect again rush current discharge from a REG capacitor or an external filter capacitor connected to the REG pin. Placing the resistor in series with the REG capacitor is an alternative to avoiding an additional drop in V_{REG} if the filter capacitor used by the external circuit is much smaller than the REG capacitor.
- 2. After VSS is connected, the device allows a random cell connection to the Vx pin.
- 3. The cell should be connected to the lower V_n pin; the unused V_n pin should be shorted to the (V_{n-1}) pin. See Figure 17 for details.

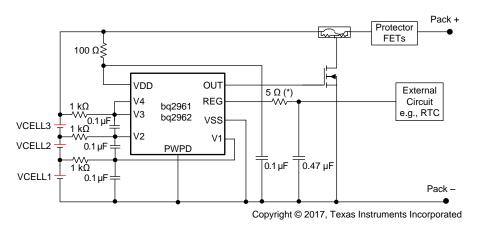


Figure 17. 3-Series BQ2961 and BQ2962 Schematic

4. A zener diode can be added to the REG pin to VSS, as shown in Figure 18. This is recommended to protect the circuit connected to the REG pin if floating VSS in the field is a risk concern. When VSS is floating (during cell connection when VSS is not connected first or in a system fault with a broken BAT- wire), the REG voltage always pulls up to VDD. In a 4-series configuration, the REG voltage can reach approximately 16 V with VSS floating. Adding a zener diode clamps the REG voltage to a safe level for the external circuits connected to the REG pin. Having the zener diode can also protect the external circuits if the REG pin is shorted to the OUT pin or any other high-voltage output terminal. If a zener diode is used, TI recommends putting the diode on the battery side with the BQ296xxx device to allow protection on the REG pin, as well as the circuit connected to REG under the floating VSS condition. The resistor in series with the REG pin is not required in this case.

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The $5\text{-}\Omega$ resistor limits the rush current discharge from the capacitor during cell connection when Vss is not connected first

This resistor is not required if Vss is connected first in the cell connection sequence.

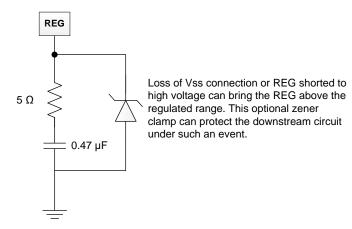
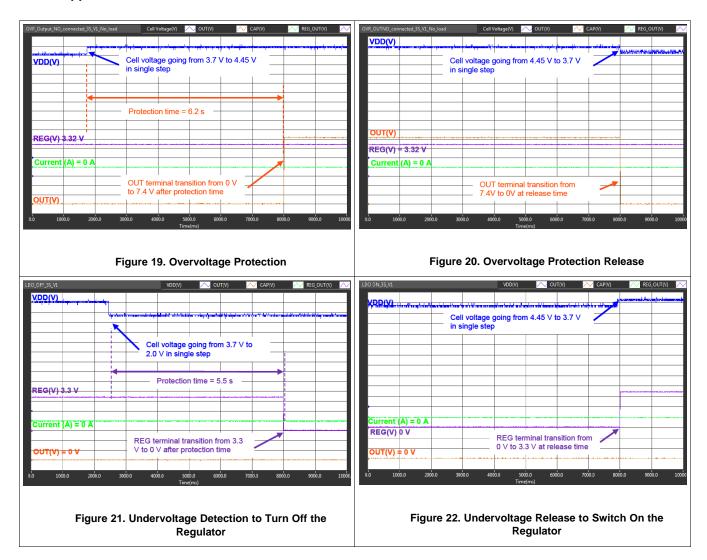


Figure 18. 5-V Zener Diode

5. For 2-series to 3-series applications, if an external control for the regulated output is required, select the BQ2960xy family. Otherwise, select the BQ2961xy family.

9.2.3 Application Curves

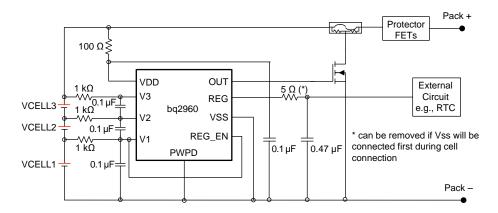


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9.2.4 Other Schematics



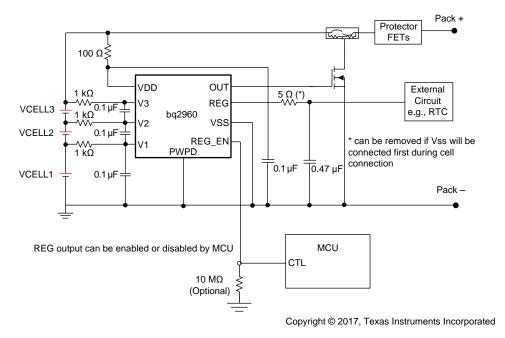


Figure 23. BQ2960 Schematic with REG Output Always Enabled



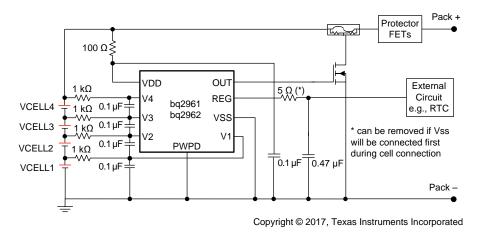


Figure 24. BQ2961 and BQ2962 Schematic

10 Power Supply Recommendations

The maximum power is 15 V for BQ2960 and 20 V for BQ2961 and BQ2962 on VDD.

NOTE
Connect VSS first during power up.

11 Layout

11.1 Layout Guidelines

Use the following layout guidelines:

- 1. Ensure the RC filters for the Vx pins and VDD pin are placed as close as possible to the target terminal, reducing the tracing loop area.
- 2. The capacitor for REG should be placed close to the device terminals.
- 3. Ensure the trace connecting the fuse to the gate, source of the NFET to the Pack– is sufficient to withstand the current during a fuse blown event.

11.2 Layout Example

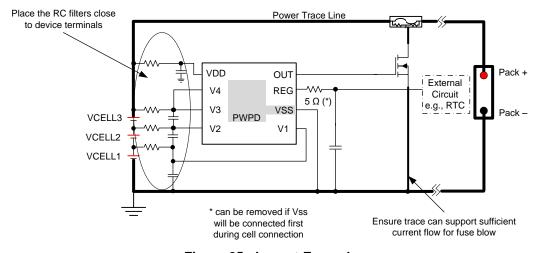


Figure 25. Layout Example



12 Device and Documentation Support

12.1 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

12.2 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E™ Online Community *TI's Engineer-to-Engineer (E2E) Community.* Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

12.3 Trademarks

E2E is a trademark of Texas Instruments.

All other trademarks are the property of their respective owners.

12.4 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

12.5 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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19-Jul-2019

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
BQ296100DSGR	ACTIVE	WSON	DSG	8	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 110	6100	Samples
BQ296100DSGT	ACTIVE	WSON	DSG	8	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 110	6100	Samples
BQ296103DSGR	ACTIVE	WSON	DSG	8	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 110	6103	Samples
BQ296103DSGT	ACTIVE	WSON	DSG	8	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 110	6103	Samples
BQ296106DSGR	ACTIVE	WSON	DSG	8	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 110	6106	Samples
BQ296106DSGT	ACTIVE	WSON	DSG	8	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 110	6106	Samples
BQ296107DSGR	ACTIVE	WSON	DSG	8	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 110	6107	Samples
BQ296107DSGT	ACTIVE	WSON	DSG	8	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 110	6107	Samples
BQ296111DSGR	ACTIVE	WSON	DSG	8	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 110	6111	Samples
BQ296111DSGT	ACTIVE	WSON	DSG	8	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 110	6111	Samples
BQ296112DSGR	ACTIVE	WSON	DSG	8	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 110	6112	Samples
BQ296112DSGT	ACTIVE	WSON	DSG	8	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 110	6112	Samples
BQ296113DSGR	ACTIVE	WSON	DSG	8	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 110	6113	Samples
BQ296113DSGT	ACTIVE	WSON	DSG	8	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 110	6113	Samples
BQ296114DSGR	ACTIVE	WSON	DSG	8	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 110	6114	Samples
BQ296114DSGT	ACTIVE	WSON	DSG	8	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 110	6114	Samples
BQ296202DSGR	ACTIVE	WSON	DSG	8	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 110	6202	Samples





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Orderable Device	Status	Package Type	Package	Pins	Package	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	(6)	(3)		(4/5)	
BQ296202DSGT	ACTIVE	WSON	DSG	8	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 110	6202	Samples
BQ296203DSGR	ACTIVE	WSON	DSG	8	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 110	6203	Samples
BQ296203DSGT	ACTIVE	WSON	DSG	8	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 110	6203	Samples
BQ296212DSGR	ACTIVE	WSON	DSG	8	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 110	6212	Samples
BQ296212DSGT	ACTIVE	WSON	DSG	8	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 110	6212	Samples
BQ296213DSGR	ACTIVE	WSON	DSG	8	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 110	6213	Samples
BQ296213DSGT	ACTIVE	WSON	DSG	8	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 110	6213	Samples
BQ296216DSGR	ACTIVE	WSON	DSG	8	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 110	6216	Samples
BQ296216DSGT	ACTIVE	WSON	DSG	8	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 110	6216	Samples
BQ296217DSGR	ACTIVE	WSON	DSG	8	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 110	6217	Samples
BQ296217DSGT	ACTIVE	WSON	DSG	8	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 110	6217	Samples
BQ296223DSGR	ACTIVE	WSON	DSG	8	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 110	6223	Samples
BQ296223DSGT	ACTIVE	WSON	DSG	8	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 110	6223	Samples
BQ296224DSGR	ACTIVE	WSON	DSG	8	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 110	6224	Samples
BQ296224DSGT	ACTIVE	WSON	DSG	8	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 110	6224	Samples

⁽¹⁾ The marketing status values are defined as follows: **ACTIVE:** Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.



PACKAGE OPTION ADDENDUM

19-Jul-2019

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead/Ball Finish Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

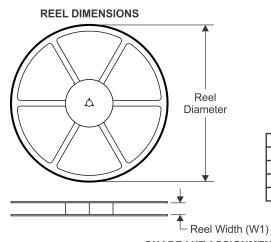
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PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION



TAPE DIMENSIONS KO P1 BO W Cavity A0

	Dimension designed to accommodate the component width
	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



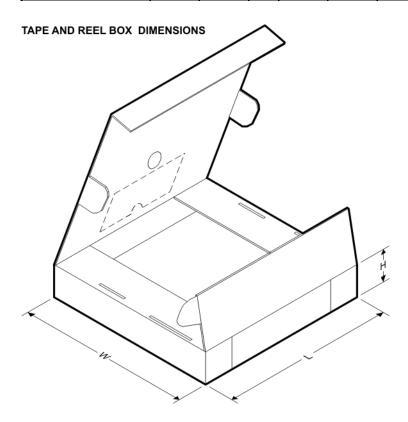
*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter		A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
					(mm)	W1 (mm)						
BQ296100DSGR	WSON	DSG	8	3000	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
BQ296100DSGT	WSON	DSG	8	250	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
BQ296103DSGR	WSON	DSG	8	3000	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
BQ296103DSGT	WSON	DSG	8	250	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
BQ296106DSGR	WSON	DSG	8	3000	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
BQ296106DSGT	WSON	DSG	8	250	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
BQ296107DSGR	WSON	DSG	8	3000	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
BQ296111DSGR	WSON	DSG	8	3000	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
BQ296111DSGT	WSON	DSG	8	250	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
BQ296112DSGR	WSON	DSG	8	3000	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
BQ296112DSGT	WSON	DSG	8	250	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
BQ296113DSGR	WSON	DSG	8	3000	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
BQ296113DSGT	WSON	DSG	8	250	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
BQ296114DSGR	WSON	DSG	8	3000	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
BQ296114DSGT	WSON	DSG	8	250	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
BQ296202DSGR	WSON	DSG	8	3000	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
BQ296202DSGT	WSON	DSG	8	250	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
BQ296203DSGR	WSON	DSG	8	3000	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2

PACKAGE MATERIALS INFORMATION

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Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
BQ296203DSGT	WSON	DSG	8	250	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
BQ296212DSGR	WSON	DSG	8	3000	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
BQ296212DSGT	WSON	DSG	8	250	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
BQ296213DSGR	WSON	DSG	8	3000	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
BQ296213DSGT	WSON	DSG	8	250	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
BQ296216DSGR	WSON	DSG	8	3000	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
BQ296216DSGT	WSON	DSG	8	250	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
BQ296217DSGR	WSON	DSG	8	3000	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
BQ296217DSGT	WSON	DSG	8	250	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
BQ296223DSGR	WSON	DSG	8	3000	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q3
BQ296223DSGT	WSON	DSG	8	250	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q3
BQ296224DSGR	WSON	DSG	8	3000	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q3
BQ296224DSGT	WSON	DSG	8	250	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q3



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
BQ296100DSGR	WSON	DSG	8	3000	210.0	185.0	35.0
BQ296100DSGT	WSON	DSG	8	250	210.0	185.0	35.0
BQ296103DSGR	WSON	DSG	8	3000	210.0	185.0	35.0
BQ296103DSGT	WSON	DSG	8	250	210.0	185.0	35.0



PACKAGE MATERIALS INFORMATION

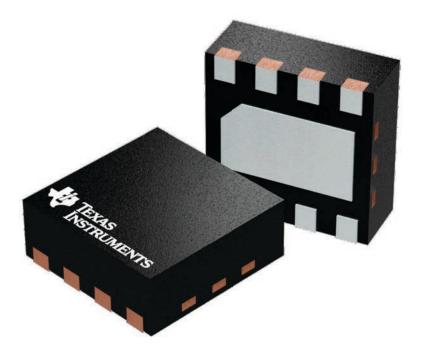
www.ti.com 20-Jul-2019

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
BQ296106DSGR	WSON	DSG	8	3000	210.0	185.0	35.0
BQ296106DSGT	WSON	DSG	8	250	210.0	185.0	35.0
BQ296107DSGR	WSON	DSG	8	3000	210.0	185.0	35.0
BQ296111DSGR	WSON	DSG	8	3000	210.0	185.0	35.0
BQ296111DSGT	WSON	DSG	8	250	210.0	185.0	35.0
BQ296112DSGR	WSON	DSG	8	3000	210.0	185.0	35.0
BQ296112DSGT	WSON	DSG	8	250	210.0	185.0	35.0
BQ296113DSGR	WSON	DSG	8	3000	210.0	185.0	35.0
BQ296113DSGT	WSON	DSG	8	250	210.0	185.0	35.0
BQ296114DSGR	WSON	DSG	8	3000	210.0	185.0	35.0
BQ296114DSGT	WSON	DSG	8	250	210.0	185.0	35.0
BQ296202DSGR	WSON	DSG	8	3000	210.0	185.0	35.0
BQ296202DSGT	WSON	DSG	8	250	210.0	185.0	35.0
BQ296203DSGR	WSON	DSG	8	3000	210.0	185.0	35.0
BQ296203DSGT	WSON	DSG	8	250	210.0	185.0	35.0
BQ296212DSGR	WSON	DSG	8	3000	210.0	185.0	35.0
BQ296212DSGT	WSON	DSG	8	250	210.0	185.0	35.0
BQ296213DSGR	WSON	DSG	8	3000	210.0	185.0	35.0
BQ296213DSGT	WSON	DSG	8	250	210.0	185.0	35.0
BQ296216DSGR	WSON	DSG	8	3000	210.0	185.0	35.0
BQ296216DSGT	WSON	DSG	8	250	210.0	185.0	35.0
BQ296217DSGR	WSON	DSG	8	3000	210.0	185.0	35.0
BQ296217DSGT	WSON	DSG	8	250	210.0	185.0	35.0
BQ296223DSGR	WSON	DSG	8	3000	210.0	185.0	35.0
BQ296223DSGT	WSON	DSG	8	250	210.0	185.0	35.0
BQ296224DSGR	WSON	DSG	8	3000	210.0	185.0	35.0
BQ296224DSGT	WSON	DSG	8	250	210.0	185.0	35.0

2 x 2, 0.5 mm pitch

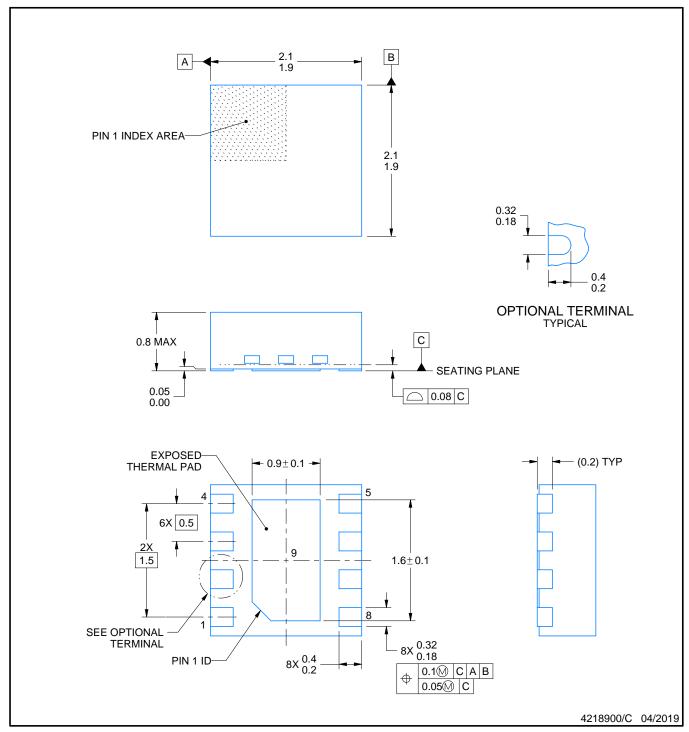
PLASTIC SMALL OUTLINE - NO LEAD

This image is a representation of the package family, actual package may vary. Refer to the product data sheet for package details.





PLASTIC SMALL OUTLINE - NO LEAD

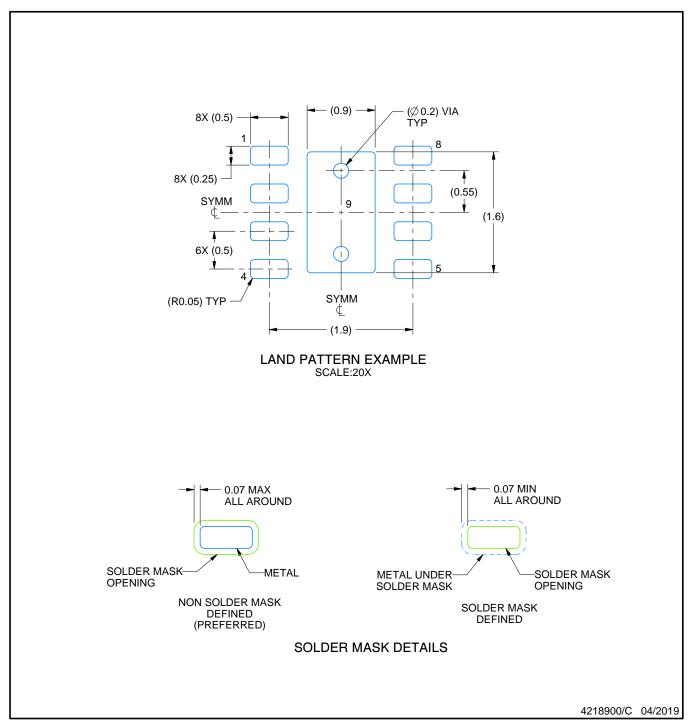


NOTES:

- All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.



PLASTIC SMALL OUTLINE - NO LEAD

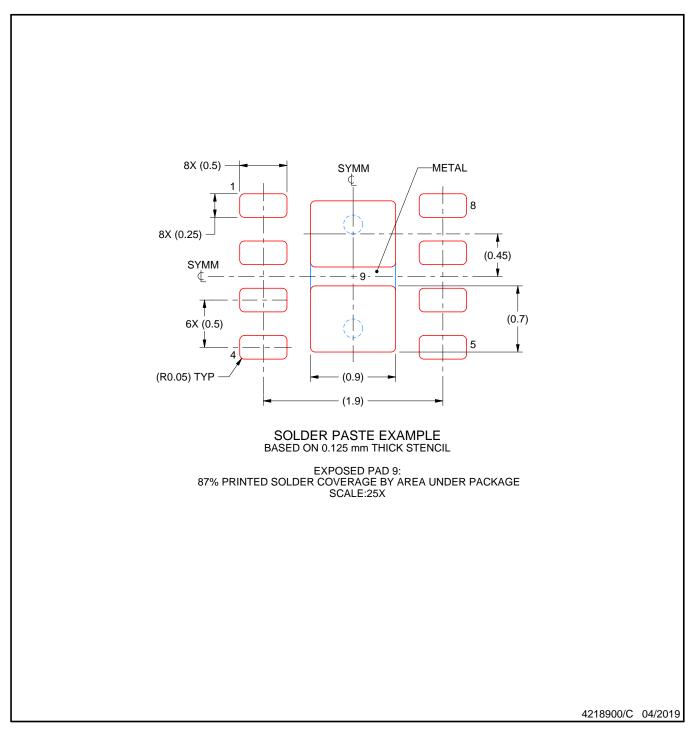


NOTES: (continued)

- 4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
- Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.



PLASTIC SMALL OUTLINE - NO LEAD



NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



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